

INFRARED DIODE LASER AT 852nm

RN-III-852L/1~150mW

产品描述

It features ultra compact design, long lifetime, cost-effectiveness and easy operation.

They are used in measurement, communication, spectrum analysis, etc.

产品参数

RN-III-852L/1~150mW		
Central wavelength (nm)		852±10
Operating mode		CW
Output power (mW)		>1, 10, 20,...,150
Power stability (rms, over 4 hours)		<1%, <2%, <3% (<0.5%, optional)
Transverse mode		Near TEM ₀₀
Dimensions of beam at the aperture (1/e ² ,mm)		~4.0
Beam divergence, full angle (mrad)		<1.0
Polarization ratio		>50:1 (>100:1, optional) Horizontal±5 degree (Vertical Optional)
Warm-up time (minutes)		<5
Pointing stability after warm-up (mrad)		<0.05
Beam height from base plate (mm)		24. 8
Operating temperature (°C)		10~35
Power supply	85-264VAC	PSU-III-LED/ PSU-III-FDA (Frequency for 1Hz-30kHz)
	100-240VAC	PSU-A-D (Frequency for 30kHz -100kHz)
TTL / Analog modulation		TTL or Analog with 1Hz-1kHz 1kHz-10kHz, 10kHz-30kHz, 30kHz-100kHz optional
Expected lifetime (hours)		10000
Warranty		1 year